

RoHS Compliant IRF ameter Max. Units VDS Drain Source VoltageV ID @ TC = C Continuous Drain Current, VGS @V ID @ TC = C Continuous Drain Current, VGS @V A IDM Pulsed Drain Current †PD @TC =°C Power Dissipation PD @TC =°C Power Dissipation Linear Derating Factor W/°C VGS Gate-to F Product details. Low RDS (on) Dynamic dv/dt Rating. Description. Title MOSFET, DUAL N-CH, V, A, SOICDescriptionDatasheet IRF Datasheet KB Description: HEXFET Power MOSFETResults. Dual N-Channel Missing: pdf This datasheet has been download from Datasheets for electronics components IRF International Rectifier HEXFET Power MOSFET. Description. Fast Switching. RoHS Compliant. Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low onresistance per silicon area. Manufacturer: Guangdong Youtai Semiconductor Co., Ltd IRF PDF File Similar Datasheet IRF Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized IRF datasheet, IRF pdf, IRF data sheet, datasheet, data sheet, pdf, International Rectifier, V Dual N-Channel HEXFET Power MOSFET in a SOpackage · IRFTRPBF Infineon Technologies MOSFETs MOSFT DUAL NChV A datasheet, inventory, & pricingKansas St., El Segundo, California, USA Tel: () TAC Fax: () Visit us at for sales contact information/04 IRF Product details. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an MOSFET (Si/SiC) N-Channel Power MOSFET. IRF IRF OverviewV Dual N-Channel HEXFET Power MOSFET in a SOpackage. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an IRF datasheet, IRF pdf, IRF data sheet, datasheet, data sheet, pdf, International Rectifier, V Dual N-Channel HEXFET Power MOSFET in a SOpackage IRF International Rectifier HEXFET Power MOSFET. Title MOSFET, DUAL N-CH,V, A, SOICIRF DatasheetKB: Distributor elementAsia-Pacific Stock IRF Datasheet (PDF)International Rectifier: Part IRF Description HEXFET Power MOSFET: File Size Kbytes: Html View Benefits. Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. The °C rating for the SOpackage provides improved thermal performance with increased safe operating area and dual MOSFET die capability make it ideal in a variety Overview V Dual N-Channel HEXFET Power MOSFET in a SOpackage. Datasheet: Kb/7P. Benefits.